Diode Module

Features

- A package of series of two diodes
- Heat transfer through alumina ceramic and metal substrate
- Welding by vacuum welding technology, which provide high reliability

Product Summary

Parameter	Value	Unit
V_{RRM}	1800	V

(@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Non-repetitive peak reverse voltage	**T_{vj} = 25°C**	**V_{RSM}**	**1900**	**V**
Average forward current	**T_C = 100°C**	**$I_{F(AV)}$**	**200**	**A**
Forward surge current	**1/2 cycle, Sine wave, 50Hz** **T_{vj} = 25**	I_{FSM}	5800	A
I^2t value for fusing		I^2t	168200	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

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Package Outlines (mm)

Unit of measurement: mm

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